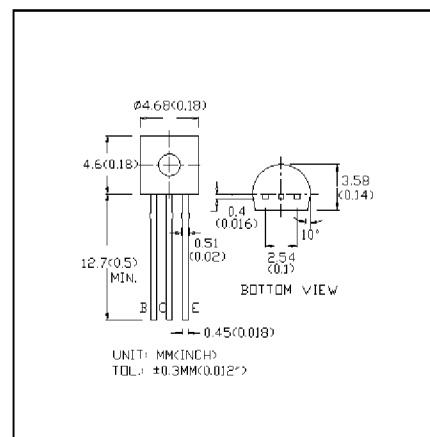


DESCRIPTION

2N5367 is PNP silicon planar transistor use in general purpose consumer and industrial amplifier and switching applications.



ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	V_{CBO}	40V
Collector-Emitter Voltage	V_{CEO}	40V
Emitter-Base Voltage	V_{EBO}	4V
Collector Current	I_C	300mA
Continuous Power Dissipation	P_d	360mW
Operating & Storage Junction Temperature	T_j, T_{stg}	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS

($T_a = 25^\circ\text{C}$)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS	
Collector-Emitter Breakdown Voltage	V_{CEO}^*	40		V	$I_C = 10\text{mA}$	$I_B = 0$
Collector Cutoff Current	I_{CBO}		100	nA	$V_{CB} = 40\text{V}$	$I_E = 0$
Collector Cutoff Current	I_{CES}		100	nA	$V_{CB} = 40\text{V}$	$V_{EB} = 0$
Emitter Cutoff Current	I_{EBO}		10	μA	$V_{EB} = 4\text{V}$	$I_C = 0$
D.C. Current Gain	H_{FE}^*	200			$I_C = 2\text{mA}$	$V_{CE} = 10\text{V}$
		250	500		$I_C = 50\text{mA}$	$V_{CE} = 1\text{V}$
		75			$I_C = 300\text{mA}$	$V_{CE} = 5\text{V}$
Base-Emitter Voltage	V_{BE}		0.8	V	$I_C = 2\text{mA}$	$V_{CE} = 10\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}^*$		0.25	V	$I_C = 50\text{mA}$	$I_B = 2.5\text{mA}$
			1	V	$I_C = 300\text{mA}$	$I_B = 30\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}^*$		1.1	V	$I_C = 50\text{mA}$	$I_B = 2.5\text{mA}$
			2	V	$I_C = 300\text{mA}$	$I_B = 30\text{mA}$
Small Signal Current Gain	h_{fe}	200			$I_C = 2\text{mA}$	$V_{CE} = 10\text{V}$
					$f = 1\text{kHz}$	
Output Capacitance	C_{ob}		8	pF	$V_{CB} = 10\text{V}$	$f = 1\text{MHz}$
Input Capacitance	C_{ib}		35	pF	$V_{EB} = 0.5\text{V}$	$f = 1\text{MHz}$
Current Gain-Bandwidth Product	f_T	200	TYP	pF	$I_C = 2\text{mA}$	$V_{CE} = 10\text{V}$

* Pulse test : pulse width $< 300\mu\text{S}$, duty cycle $< 2\%$.



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